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Applicant(s): Hyungjun KIM et al.

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U.S. PATENTS

Initials	Patent Number	Issue Date	Name	Class	Sub-class	Filing date
QJ	2003/0201537A	10/30/03	Lane et al.			
QJ	U.S. Patent Application Serial No. 10/699,226		KIM et al.			

FOREIGN PATENT DOCUMENTS

Initials	Document Number	Date	Country	Name	Translation? Yes/No/n/a

OTHER DOCUMENTS (Title, Author, Date, Pages, Etc., if known)

QJ	Rossnagel et al., Plasma-enhanced atomic layer deposition of Ta and Ti for inter-connect diffusion barriers, J. Vac. Sci. Technol. B 18(4), July/Aug 2002
QJ	KIM et. al., Growth of cubic-Ta _N thin films. J. App. Physics, Vol. 92, No. 12, 2002
QJ	Kim et al., Growth kinetics and initial stage growth during plasma-enhanced Ti atomic layer deposition, J. Vac. Sci. Technol. A 20(3), May/June 2002
QJ	Kim et al., Diffusion barrier properties of transition metal thin films grown by plasma-enhanced atomic layer deposition, J. Vac. Sci. Technol. B 20(4), J/A 2002

Examiner's Signature: *Radio C. Swensens*Date Considered: *05/12/05*

Initial if reference was considered, whether or not citation is in conformance with MPEP. Mark through citation if not considered.
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